



Mr. Kevin Kyuheon Cho

(onsemi, Korea)

Kevin received the bachelor's degree in electrical engineering from Yonsei University in 2006 and the master's degree in electrical engineering from Seoul National University in 2008. He joined Samsung Electronics, Semiconductor R&D in 2008 as a device engineer. He went through plenty of design experiences regarding BCD, Discrete, and Memory technologies based on TCAD simulation in Samsung. In 2017, he started to lead 130nm BCDLite technology development as a device engineer in GlobalFoundries, and successfully released the next generation high voltage devices such as LDMOS, BJT, Diode and ESD. He joined SiC technology development group at ON Semiconductor in 2018. He is currently leading the development of Gen2 SiC MOSFET and Gen3 SiC JBS Diode.